

1 Product features

- Low offset voltage
 - $2\mu V$ (the typical)
 - 10µV(Max value)
- Zero drift: 0.05µV/°C (max. value)
- Low power consumption
 - $17\mu A$ (single channel)
 - 30µA(dual channels)
- Rail-to-rail input/output
- Wide working voltage ranges: 1.8V- 5.5V
- Low 0.1Hz-10Hz noise: 1.1µV
- Volt Current Condenser

2 Typical applications

- Sensor
- Temperature detection
- Electronic scale
- Bridge circuit reading
- Medical instrument

Zero Drift, Micro-power Consumption CMOS Operational Amplifier

3. General Description

SLAx333 is a CMOS operational amplifier with single power supply and micro power consumption, which can realize rail to rail input/output. The self-calibration

technology is adopted to provide extremely low offset

 $voltage 2\mu V ~(\mbox{the typical})~;$ at the same time, the drifting

along with temperature and time is near to zero. The

amplifier can provide high input resistance (the scope of common mode is 100mV higher than the power rail voltage) Single power supply or dual power supply of $1.8V (\pm 0.9V)$ and even $5.5V (\pm 2.75V)$ can be adopted. The SLAx333 series of products can provide excellent

CMRR performance, with no interaction associated with

the traditional mutually complemented input level. The

design can achieve excellent performance during driving the analog-digital converter (ADC) by not reducing the differential linearity.

SLA2333 (single-channel version) can provide 5-pin SOT-23-5, SC 70-5 and SOIC-8 package. SLA333 (dual-channel version) can provide SOIC-8, MSOP-8 and DFN- $2\times2-8$ package.



4 Definition of pins and information of signs



top view IN+ 1 V- 2 IN- 3 SC70-5

SLA2333









	Pins			I/O	Description	
Name	SOIC	SOT	SC70	1/0	Description	
IN+	3	3	1	Ι	Same-phase input	
IN-	2	4	3	Ι	Inverted-phase input	
NC	1, 5, 8	_	_	_	No internal chain (can be suspended in midair)	
OUT	6	1	4	0	Output	
V+	7	5	5	_	Positive power supply (the highest)	
V-	4	2	2	_	Negative power supply (the lowest)	

Functions of pins: SLA2333

Functions of pins: SLA333

Pins			I/O	Description
Name	DFN	SOIC、MSOP-8	1/0	Description
INA+	3	3	Ι	Same-phase input, channel A
INA-	2	2	Ι	Inverted-phase input, channel A
INB+	5	5	Ι	Same-phase input, channel B
INB-	6	6	Ι	Inverted-phase input, channel B
OUTA	1	1	0	Output, channel A
OUTB	7	7	0	Output, channel B
V+	8	8		Positive power supply (the highest)
V-	4	4		Negative power supply (the lowest)



5 Specification

5.1 Absolute Max. rated value

Please refer to⁽¹⁾

	Min	Max	Unit
Supply voltage	6.5		V
Analog input voltage	V0.2	$V_{+} + 0.2$	V
Operating junction temperature, TJ		150	°C
Storage Temperature, T _{stg}	-65	150	°C

(1)The stress of the listed values exceeding the absolute max. rated values may lead to permanent damages to the device. Such are working conditions at the rated value of stress. Functional operations of the device under the rated values and any other operation other than suggested working conditions are not indicated here. Long-time working at the absolute rated conditions may lead to influences on reliability of the chip.

5.2 ESD Rated value

ESD	Values	Unit
НВМ	7K	v

5.3 Working conditions

	Min	Max	Unit
Supply voltage	1.8	5.5	V
Rated temperature range	-40	125	°C



6 Electrical parameters (@TA=+25°C, Vcm=Vs/2, VOUT=Vs/2, unless otherwise specified)

Item	Parameter description	Working conditions	Min	Typica l value	Max	Unit	
Output char	acteristics				·		
Vos	Offset voltage	Vs=5V		2	10	μV	
dVos/dT	Low input offset voltage	$TA = -40^{\circ}C \text{ to } 125^{\circ}C$		0.02	0.05	µV/°C	
IB	Bias current			±100		pА	
Ios	offset current			±120		pА	
V _{CM}	Common-mode input voltage ranges		(V–) – 0.1		(V+) + 0.1	V	
CMRR	Common mode rejection ratio	$(V-) - 0.1V < V_{CM} < (V+) + 0.1V,$ $T_A = -40^{\circ}C \text{ to } 125^{\circ}C$		120		dB	
Aol	Open loop voltage gain	$(V-) + 100mV < V_O < (V+) - 100mV, \label{eq:V-}$ $R_L = 10k\Omega, \ T_A = -40^\circ C \ to \ 125^\circ C$		120		dB	
Output cha	racteristics						
Output s with the	wing when compared power supply rail	R _L =10K		30	70	mV	
Isc	Short circuit			±17		mA	
Power sup	ply						
Vs	Supply voltage ranges		1.8		5.5	V	
IQ	Quiescent power	IO=0A, TA= -40°C to 125°C (single operational amplifier)		17		μΑ	
	consumption	IO=0A, TA= -40°C to 125°C (dual operational amplifier)		30		μΑ	
PSRR	Volt Current Condenser	Vs=1.8V to 5.5V, T_{A} = -40°C to 125°C		1	5	$\mu V/V$	
Opening ti	me	V _S =+5V		200		μs	
Frequency of	haracteristics				•		
GBW	Gain bandwidth product	C _L =100pF		350		KHz	
SR	Slew rate	G=1		0.16		V/µs	
Noise coeff	Noise coefficient						
Input		F=0.1Hz to 10Hz		1.1		μV_{PP}	
Temperatur	e						
T _A	Rated temperature range		-40		125	°C	







Figure 1 Offset voltage production distribution



Figure 2 Noises from 0.1Hz to 10Hz



Figure 3 Large signal step response



Figure 5 Negative overvoltage recovery



Figure 4 Small signal step response



Figure 6 Positive overvoltage recovery





Figure 7 Relationship between quiescent current and temperature







8 Application guide

With the characteristic of unit gain stability, SLAx333 series of operational amplifiers are applicable to various general applications. SLAx333 can provide very low offset voltage and realize extremely low temperature drift with changes in time and temperature.

8.1 Working voltage

SLAx333 series of operational amplifiers can be powered with both single power supply of 1.8V to 5.5V and dual power supplies of $\pm 0.9V$ to $\pm 2.75V$. The supply voltage higher than +6.5V (absolute maximum value) will lead to permanent damages to the device. In order to achieve better performance, it is necessary to set a shunt capacity of 0.1µF near to the power supply pin.

8.2 Rail to rail input and output

SLAx333 series of operational amplifiers have the characteristic of rail-to-rail input and rail-to-rail output. The complementary input pair structure can achieve very wide input common mode voltage scope (100mV higher than the power supply rail). In the resistive load of $10k\Omega$, the output voltage swing can achieve 100mV lower than the voltage of the power supply rail.

8.3 Input

SLAx333 series of operational amplifiers have two internal ESD protective diodes on the input end, connected between the power supply rail and input, as shown in Figure 9. When the input voltage is 300mV higher than any power rail, the diodes positively break over to amplify the current to protect the internal devices. Generally, the input bias current is about 100pA; however, the input voltage higher than the supply voltage may lead to flowing of the over-current into or out of the pin, and it may lead to permanent damages to the devices if the current is higher than 10mA. Input resistance can be used to realize easy limitation, as shown in Figure 10.



Figure 9 Input ESD structure

Figure 10 Input current protection

8.4 Internal bias correction

With the chopped wave self-calibration technology and the continuous time signal chain technology, SLAx333 series of operational amplifiers can make offset correction once every about 10µs. The amplifiers need about 200µs to achieve the rated Vos accuracy after start-up. In addition, the chopped wave self-calibration technology can eliminate the flicker noise.

8.5 Residual ripple waves

SLAx333 series of operational amplifiers can eliminate the offset voltage with the chopped wave self-calibration technology; at the same time, SLAx333 can filter the ripple waves caused by chopped wave modulation with the notching filter. Although the ripple wave voltage is restrained, there is still relatively large residual noise energy on chopped wave frequency and the harmonic component. In order to filter the noise at the wave frequency in a more favorable way, it is recommended to set a post-filter at the output end of the operational amplifiers.



9 Typical applications

9.1 Temperature measurement

Figure 11 shows the application of temperature measurement.



Figure 11. Temperature measurement

9.2 Thermistor measurement

SLA2333

Figure 12 shows the application of thermistor measurement.



Figure 12. Thermistor measurement



9.3 Low-end current monitoring

Figure 13 shows the application of low-end current monitoring.



Figure 13. Low end current monitoring

9.4 High end current monitoring

Figure 14 shows the application of high-end current monitoring.



NOTES:(1)Zener rated for op amp supply capability (2)Current-limiting resistor. (3)Chhose Zener biasing resistor or dual NMOSFETs

Figure 14. High end current monitoring



9.5 Instrument amplifier

Figure 15 shows the application of instrument amplifier.



Figure 15. Instrument amplifier



Package size profile drawing

SOT23-5



	Dimensions in		Dimensions in		
Symbol	Millir	neters	Inches		
	Min	Max	Min	Max	
А	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
с	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
Е	2.650	2.950	0.104	0.116	
E1	1.500	1.700	0.059	0.067	
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



SC70-5(SOT353)





Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
А	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
с	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
Е	2.150	2.450	0.085	0.096
E1	1.150	1.350	0.045	0.053
e	0.650	TYP.	0.026	TYP.
e1	1.200	1.400	0.047	0.055
L	0.300	0.600	0.012	0.024
L1	0.525 REF.		0.021	REF.
θ	0°	8°	0°	8°



SOIC-8(SOP-8)





	Dimensions in		Dimensions in		
Symbol	Millimeters		Inches		
	Min	Max	Min	Max	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
e	1.270 TYP.		0.050	TYP.	
L	0.400	0.800	0.016	0.031	
θ	0°	8°	0°	8°	



MSOP-8





Symbol	Dimen Millin	Dimensions in Millimeters		Dimensions in	
Symbol	Min	Max	Min	Max	
А	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
С	0.090	0.230	0.004	0.015	
D	2.900	3.100	0.114	0.122	
Е	4.750	5.050	0.187	0.199	
E1	2.900	3.100	0.114	0.122	
e	0.650 TYP.		0.026	TYP.	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	б°	



DFN-8 2*2







	Dimensions in		Dimensions in	
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
А	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203	REF.	0.008 REF.	
D	1.900	2.100	0.075	0.083
Е	1.900	2.100	0.075	0.083
D1	0.500	0.700	0.020	0.028
E1	1.100	1.300	0.043	0.051
K	0.350	REF.	0.014	REF.
b	0.200	0.300	0.008	0.012
e	0.500 BSC.		0.020	BSC.
L	0.274	0.426	0.011	0.017